## **NPN Silicon Phototransistor**

### **OP600 Series**



#### Features:

- Narrow receiving angle
- Variety of sensitivity ranges
- Enhanced temperature range
- PC Board Mounting
- Mechanically and spectrally matched to OP123 and OP223 LEDs
- TXV and S level processing available



#### **Description:**

Each device in this series is a NPN silicon phototransistor in a hermetically sealed pill package. The narrow receiving angle provides excellent on-axis coupling.

The **OP600** series devices are 100% production tested using infrared light for close correlation with OPTEK GaAs and GaAlAs emitters. Components in the OP600 series are mechanically and spectrally matched to the OP123 and OP233 series.

TXV and S level components are available. For more information, please contact your local representative or OPTEK.

Please refer to Application Bulletin 210 for additional thermal information, and to Application Bulletin 202 for pill-type soldering to PC Board.

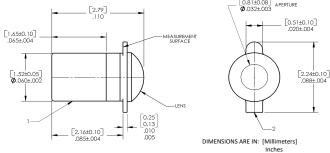
#### **Applications:**

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- High Voltage Isolation applications
- Machine safety
- End of travel sensor
- Door sensor

Ordering Information									
Part Number	Sensor	Light Current I <sub>C(ON)</sub> (mA) Min / Max	Input Power E <sub>E</sub> (mW/cm²)	Viewing Angle					
OP600A		1.20 / NA							
OP600B		0.60 / 1.80	2.5						
OP600C	Transistor	0.30 / NA		35°					
OP643SL		4.00 / 8.00	20.0						
OP644SL		7.00 / 22.00	20.0						

Pin#	Sensor		
1	Collector		
2	Emitter		







## **NPN Silicon Phototransistor**

### **OP600 Series**



### **Electrical Specifications**

#### Absolute Maximum Ratings (T<sub>A</sub> = 25° C unless otherwise noted)

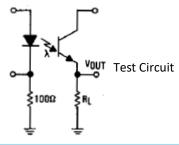
Collector-Emitter Voltage	25 V
Emitter-Collector Voltage	5 V
Storage Temperature Range	-65° C to +150° C
Operating Temperature Range	-65° C to +125° C
Soldering Temperature (5 seconds with soldering iron) (1)(2)	260° C
Power Dissipation <sup>(3)</sup>	50 mW
Continuous Collector Current	50 mA

#### Electrical Characteristics (T<sub>A</sub> = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
I <sub>C(ON)</sub> (4)	On-State Collector Current <sup>(5)</sup> OP600A OP600B OP600C	1.2 0.6 0.3		1.8 1.8 1.8	mA	V <sub>CE</sub> = 5 V, E <sub>E</sub> = 2.5 mW/cm <sup>2</sup>
	OP643SL <sup>(6)</sup>	4.0	ı	8.0		$V_{CE} = 5 \text{ V, } E_E = 20 \text{ mW/cm}^2$
I <sub>CEO</sub>	Collector-Dark Current	-	ı	100	nA	$V_{CE} = 10 \text{ V}, E_{E} = 0$
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	25	ı	-	V	I <sub>C</sub> = 100 μA
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5	-	-	V	Ι <sub>Ε</sub> = 100 μΑ
V <sub>CE(SAT)</sub> (4)	Collector-Emitter OP600 (A, B, C) <sup>(5)</sup> OP643-644 (SL) <sup>(6)</sup>	-	ı	0.4	V	$I_C = 0.15 \text{ mA}, E_E = 2.5 \text{ mW/cm}^2$ $I_C = 0.4 \text{ mA}, E_E = 20 \text{ mW/cm}^2$
t <sub>r</sub>	Rise Time	1	15	-	μs	$V_{CC}$ = 5 V, $I_C$ = 0.80 mA, $R_L$ = 1 k $\Omega$ , See Test Circuit
t <sub>f</sub>	Fall Time	-	15	-	μs	$V_{CC}$ = 5 V, $I_C$ = 0.80 mA, $R_L$ = 1 k $\Omega$ , See Test Circuit

#### Notes:

- (1) Refer to Application Bulleting 202, which discusses proper techniques for soldering pill-type devices to PC Boards.
- (2) No clean or low solids. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (3) Derate linearly 0.5 mW/° C above 25° C.
- (4) Junction temperature maintained at 25° C.
- (5) For OP600A, OP600B and OP600C, light source is a GaAIAs LED, peak wavelength = 890 nm, that provides irradiance of 2.5 mW/cm<sup>2</sup>. The source irradiance is not necessarily uniform over the entire lens area of the unit being tested.
- (6) For OP643SL and OP644SL, light source is an unfiltered tungsten bulb operating at CT = 2870 K or equivalent infrared source.

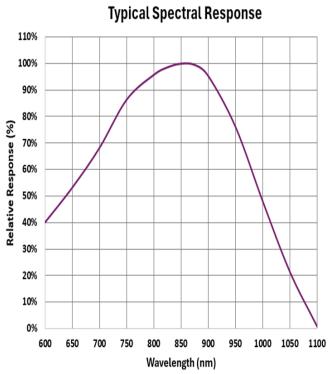


## **NPN Silicon Phototransistor**

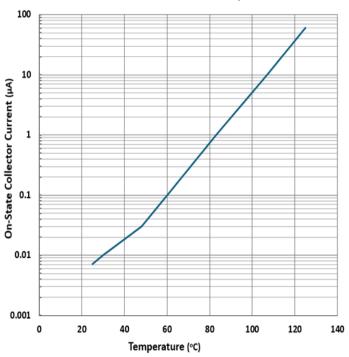
# **OP600 Series**



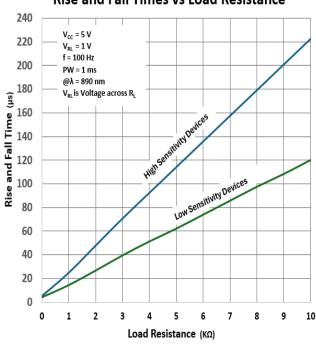
## **Typical Performance**



### **Collector Dark Current vs Temperature**



#### Rise and Fall Times vs Load Resistance



### **Normalized Collector Current vs Angular Displacement**

